Advanced PECVD-Nitride2 (HF n=2.00, 9.3nm/min)				Advanced PECVD Typical Film Properties
SiN depostion~2400A, 300C				Calibrated every 2-4 weeks
Step1:	NITRIDE2 coat			Check for the latest update on UCSB Nanofab WIKI
	Name	Value	Changeable	
	Process pressure	800 mtorr	N	
	RF setpoint	30 W	N	
	stabilization time	15 seconds	N	
	step time(m)	10	Y	
	step time(s)	0	Y	
	2%SiH4 %He	1040	N	
	N2	980	N	
	NH3	17	N	
Step2:	NITRIDE2 deposition			Nitride2~2400A Typical Film Properties
	Name	Value	Changeable	Deposition rate~8nm/min
	Process pressure	800 mtorr	N	Refractive index@632.8nm=1.961
	RF setpoint	30 W	N	Stress=500MPa
	stabilization time	15 seconds	N	HF etch rate=48nm/min
	step time(m)	30	Y	All size particles accumulated in deposition (min=87, max=303)
	step time(s)	0	Y	Mostly small size particles (0.160-0.213)um
	2%SiH4 %He	1040	N	Uniformity within the wafer (97.52-99.95)%
	N2	980	N	
	NH3	17	N	
Step3:	STANDARD PLASMA CLEAN			
	1. pump down			
	Name	Value	Changeable	
	stabilization time	15 seconds	N	
	step time(m)	0	N	
	step time(s)	30	N	
	2. Pre-purge			
	Name	Value	Changeable	
	purge	1 (Yes/No)	N	
	stabilization time	15 seconds	N	
	step time(m)	1	N	
	step time(sec)	0	N	
	3.1 High Pressure			
	Name	Value	Changeable	
	Cload position	50%	N	
	Ctune position	50%	N	
	Drive Match	1 (Yes/No)	N	
	Process pressure	600 mtorr	N	
	RF setpoint=300	300 W	N	
	Stabilization time	35 seconds	N	
	step time(m)	ENTER TIME	Y	For 7min(coat+deposition) run 1min Standard Plasma Clean
	step time(s)	0	Y	Run longer clean, (10-20%) more, only if chamber does not look clean
	CF4/O2(5)	500 sccm	N